



# STB55NF06, STP55NF06, STP55NF06FP

N-channel 60 V, 0.015  $\Omega$ , 50 A STripFET™ II Power MOSFET in D<sup>2</sup>PAK, TO-220 and TO-220FP packages

Datasheet — production data

## Features

Order code	V <sub>DSS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STB55NF06	60 V	< 0.018 $\Omega$	50 A
STP55NF06			
STP55NF06FP			50 A <sup>(1)</sup>

1. Refer to soa for the max allowable current value on FP-type due to R<sub>th</sub> value

- 100% avalanche tested
- Exceptional dv/dt capability

## Applications

- Switching application

## Description

These Power MOSFETs have been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the devices suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

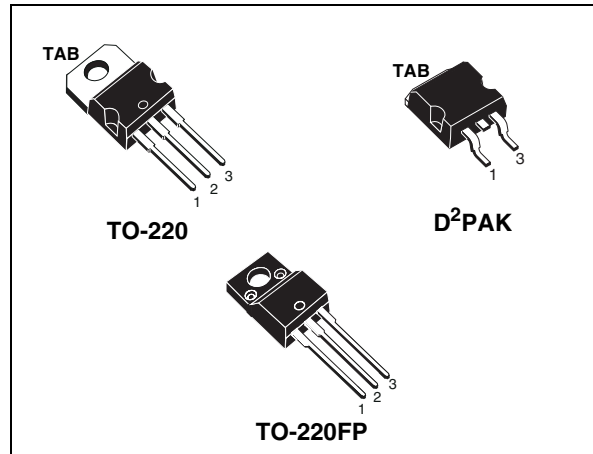
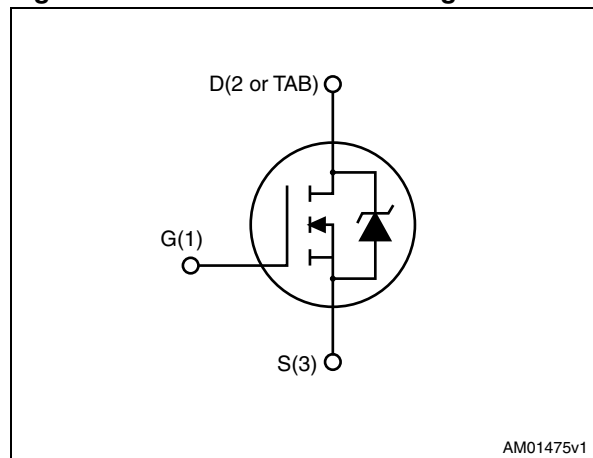


Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order code	Marking	Package	Packaging
STB55NF06	B55NF06	D <sup>2</sup> PAK	Tape and reel
STP55NF06	P55NF06	TO-220	Tube
STP55NF06FP	P55NF06FP	TO-220	

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuit</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>16</b>
<b>6</b>	<b>Revision history</b> .....	<b>18</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220, D <sup>2</sup> PAK	TO-220FP	
V <sub>DS</sub>	Drain-source voltage	60		V
V <sub>GS</sub>	Gate- source voltage	± 20		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	50	50 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	35	35 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	200	200 <sup>(1)</sup>	A
P <sub>tot</sub>	Total dissipation at T <sub>C</sub> = 25 °C	110	30	W
	Derating factor	0.73	0.20	W/°C
E <sub>AS</sub> <sup>(3)</sup>	Single pulse avalanche energy	340		mJ
dv/dt <sup>(4)</sup>	Peak diode recovery voltage slope	7		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (DC)		2500	V
T <sub>stg</sub>	Storage temperature	-55 to 175		°C
T <sub>j</sub>	Max. operating junction temperature			

1. Refer to soa for the max allowable current value on FP-type due to R<sub>th</sub> value
2. Pulse width limited by safe operating area.
3. Starting T<sub>j</sub> = 25 °C, V<sub>DD</sub> = 30 V, I<sub>D</sub> = 25 A
4. I<sub>SD</sub> ≤ 50 A, di/dt ≤ 400 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK	TO-220	TO-220FP	
R <sub>thj-case</sub>	Thermal resistance junction-case max	1.36		5	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	62.5			°C/W

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}$ , $V_{GS} = 0$	60			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 60 \text{ V}$ $V_{DS} = 60 \text{ V}$ , @ $T_J = 125^{\circ}\text{C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10 \text{ V}$ , $I_D = 27.5 \text{ A}$		0.015	0.018	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25 \text{ V}$ , $f = 1\text{MHz}$ , $V_{GS} = 0$	-	1300		pF
$C_{oss}$	Output capacitance			300		pF
$C_{rss}$	Reverse transfer capacitance			105		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30 \text{ V}$ , $I_D = 27.5 \text{ A}$ $R_G = 4.7 \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 15</a> )	-	20		ns
$t_r$	Rise time			50		ns
$t_{d(off)}$	Turn-off delay time			36		ns
$t_f$	Fall time			15		ns
$Q_g$	Total gate charge	$V_{DD} = 48 \text{ V}$ , $I_D = 55 \text{ A}$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 16</a> )	-	44.5	60	nC
$Q_{gs}$	Gate-source charge			10.5		nC
$Q_{gd}$	Gate-drain charge			17.5		nC

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		50 200	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 50 \text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 50 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 30 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 17</a> )	-	75 170 4.5		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D<sup>2</sup>PAK

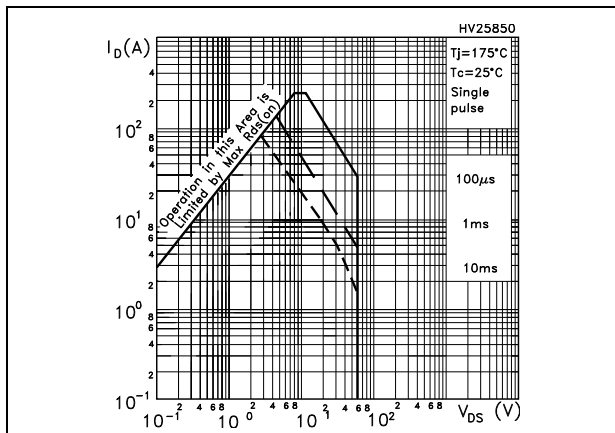


Figure 3. Thermal impedance for TO-220, D<sup>2</sup>PAK

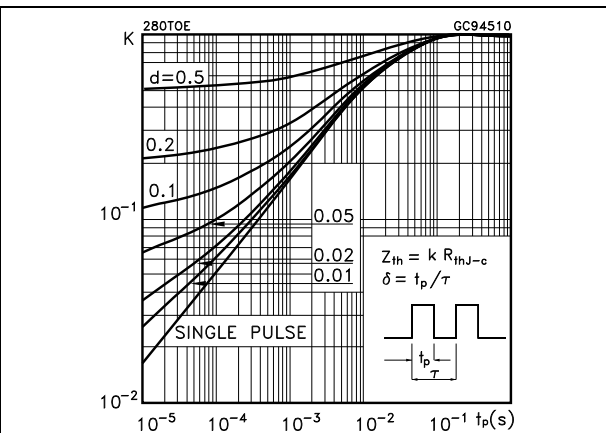


Figure 4. Safe operating area for TO-220FP

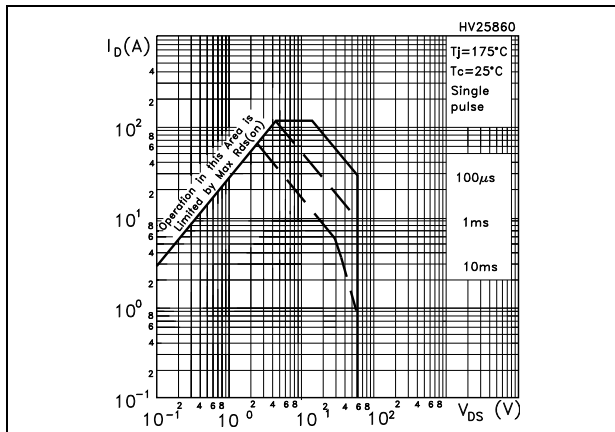


Figure 5. Thermal impedance TO-220FP

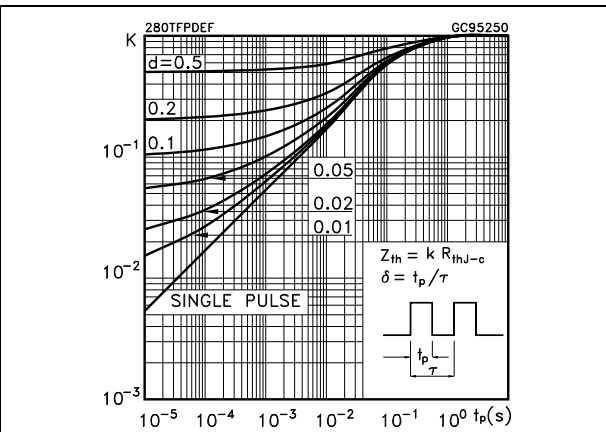


Figure 6. Output characteristics

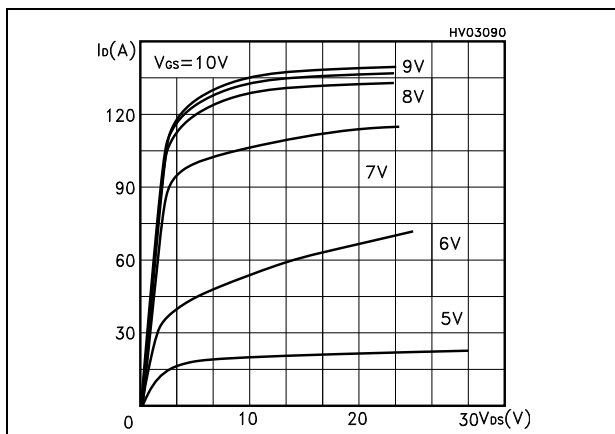


Figure 7. Transfer characteristics

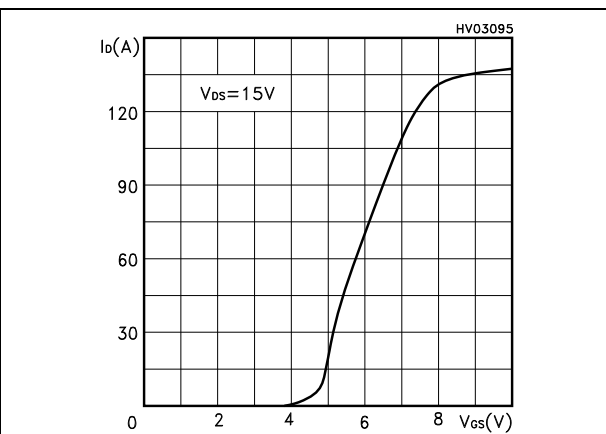


Figure 8. Transconductance

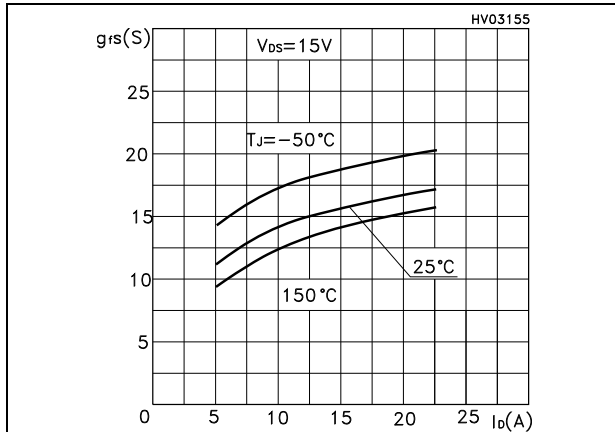


Figure 9. Static drain-source on-resistance

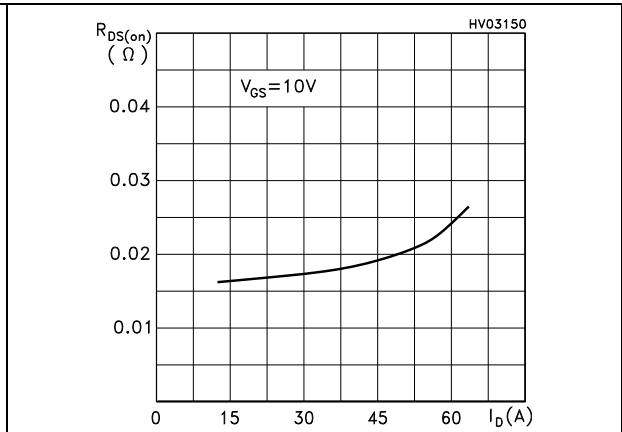


Figure 10. Gate charge vs gate-source voltage

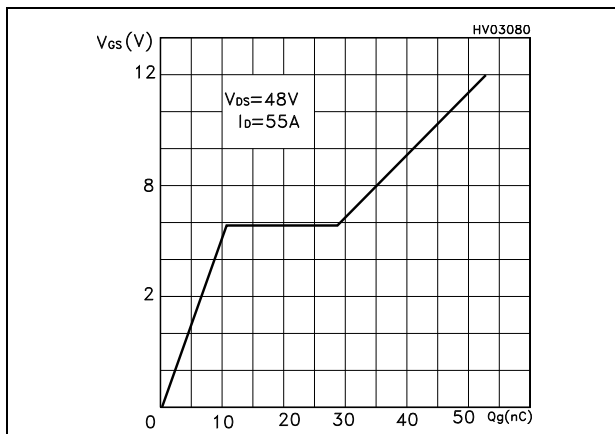


Figure 11. Capacitance variations

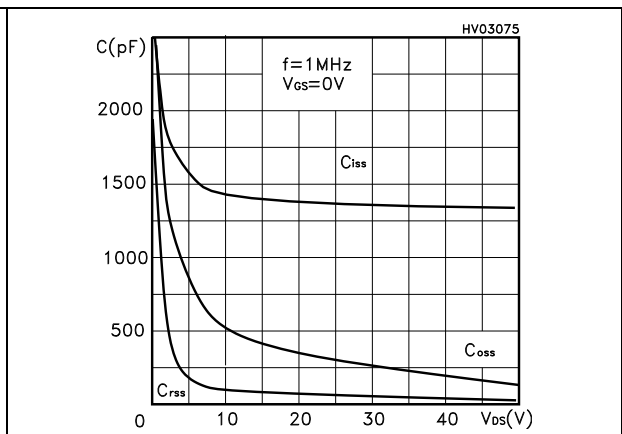


Figure 12. Normalized gate threshold voltage vs temperature

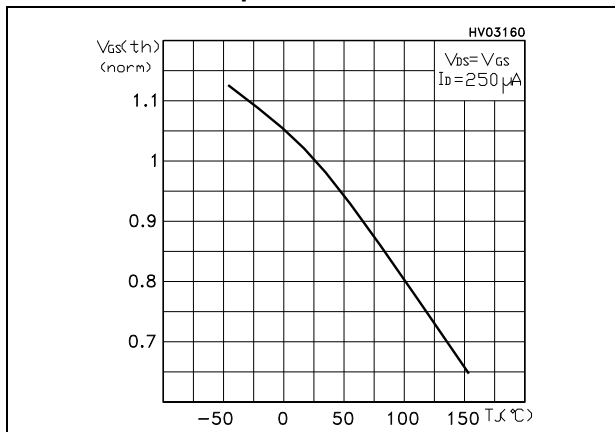


Figure 13. Normalized on-resistance vs temperature

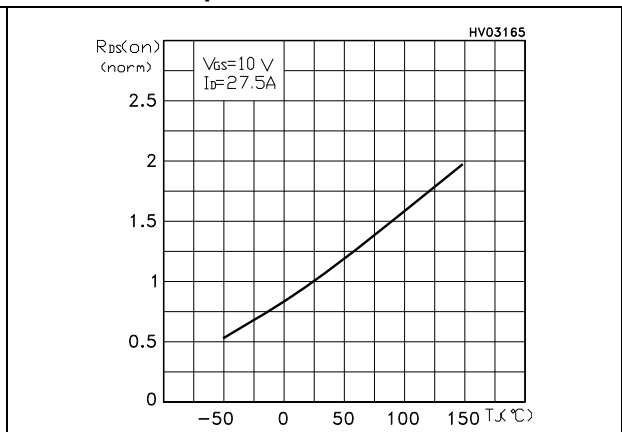
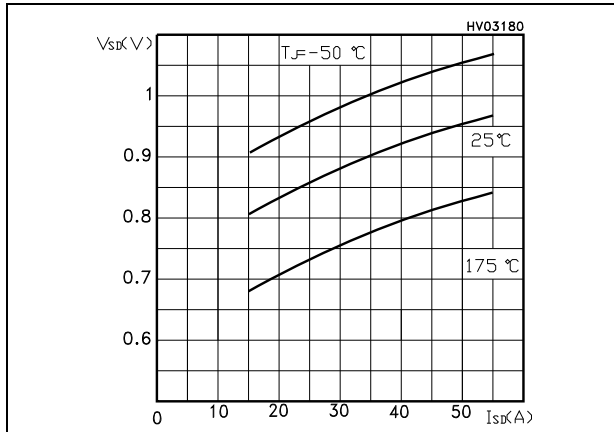


Figure 14. Source-drain diode forward characteristics



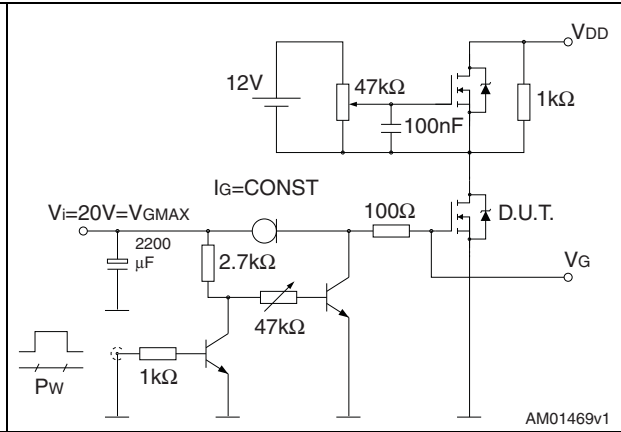


### 3 Test circuit

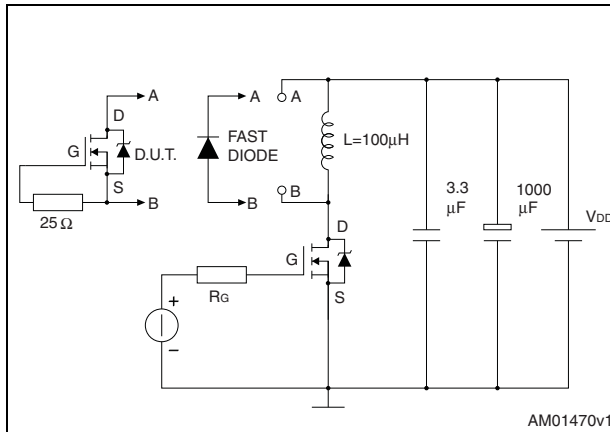
**Figure 15. Switching times test circuit for resistive load**



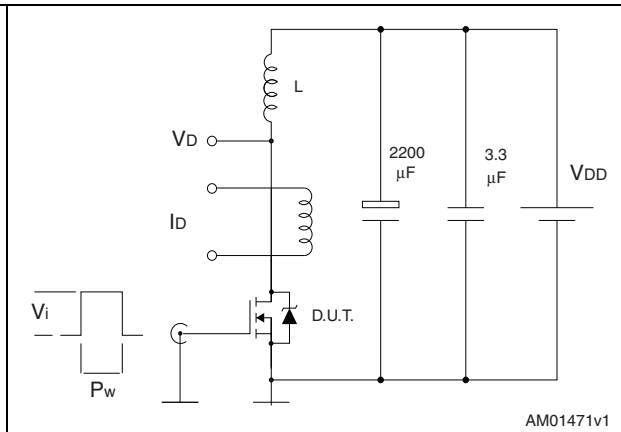
**Figure 16. Gate charge test circuit**



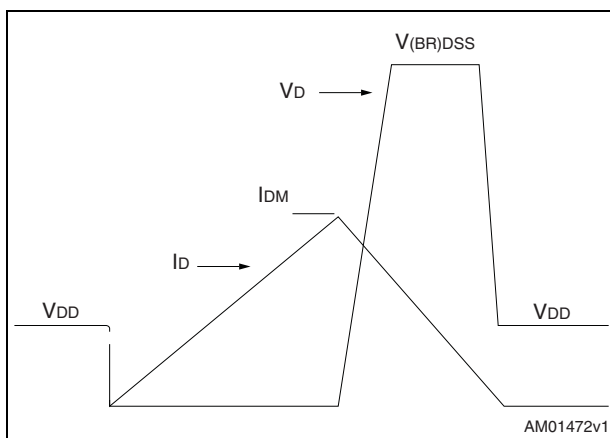
**Figure 17. Test circuit for inductive load switching and diode recovery times**



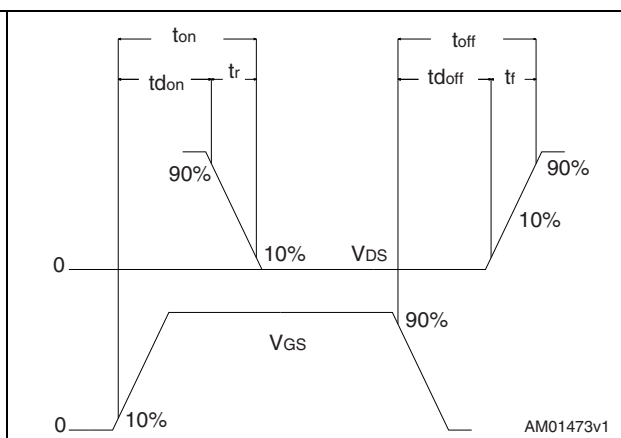
**Figure 18. Unclamped inductive load test circuit**



**Figure 19. Unclamped inductive waveform**



**Figure 20. Switching time waveform**



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

**Table 7. D<sup>2</sup>PAK (TO-263) mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 21. D<sup>2</sup>PAK (TO-263) drawing



Figure 22. D<sup>2</sup>PAK footprint<sup>(a)</sup>

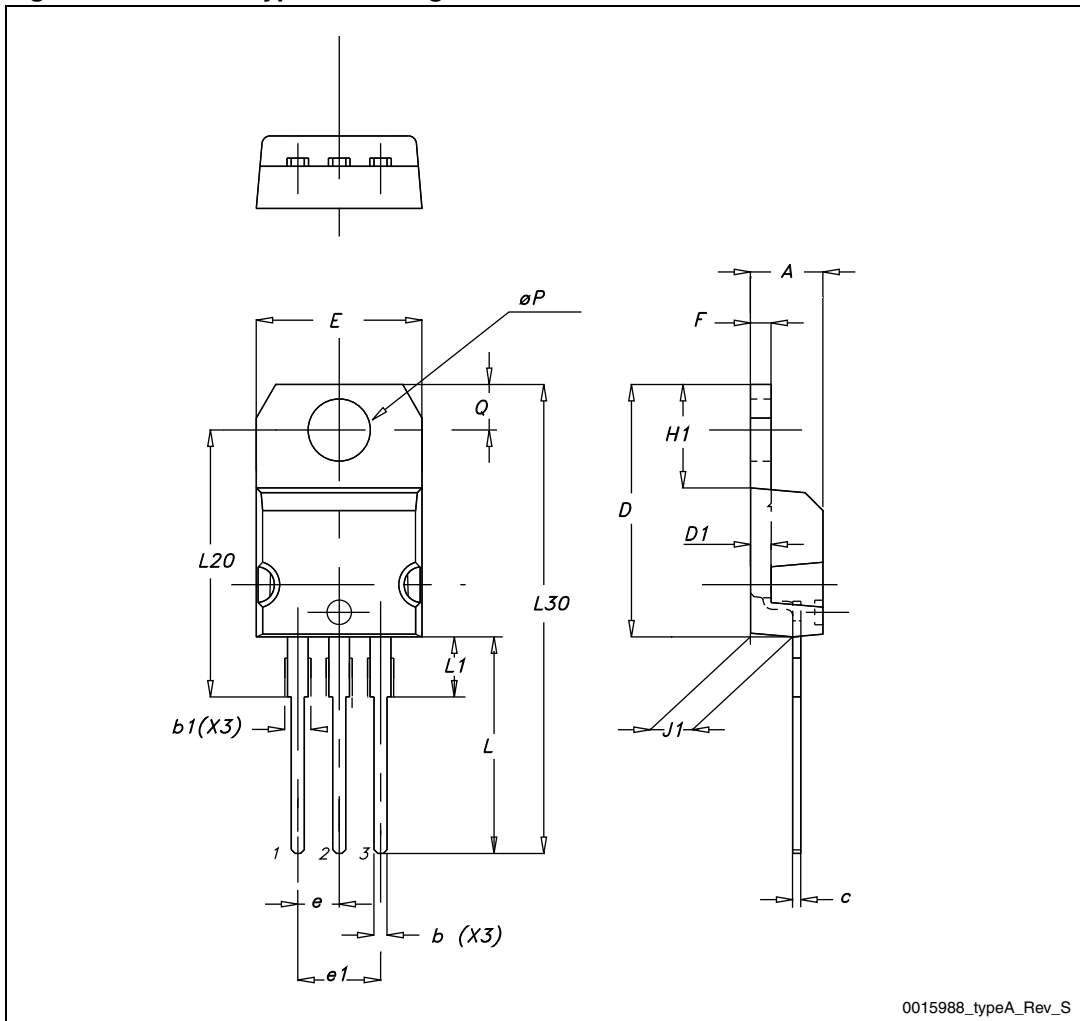


a. All dimensions are in millimeters

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 23. TO-220 type A drawing

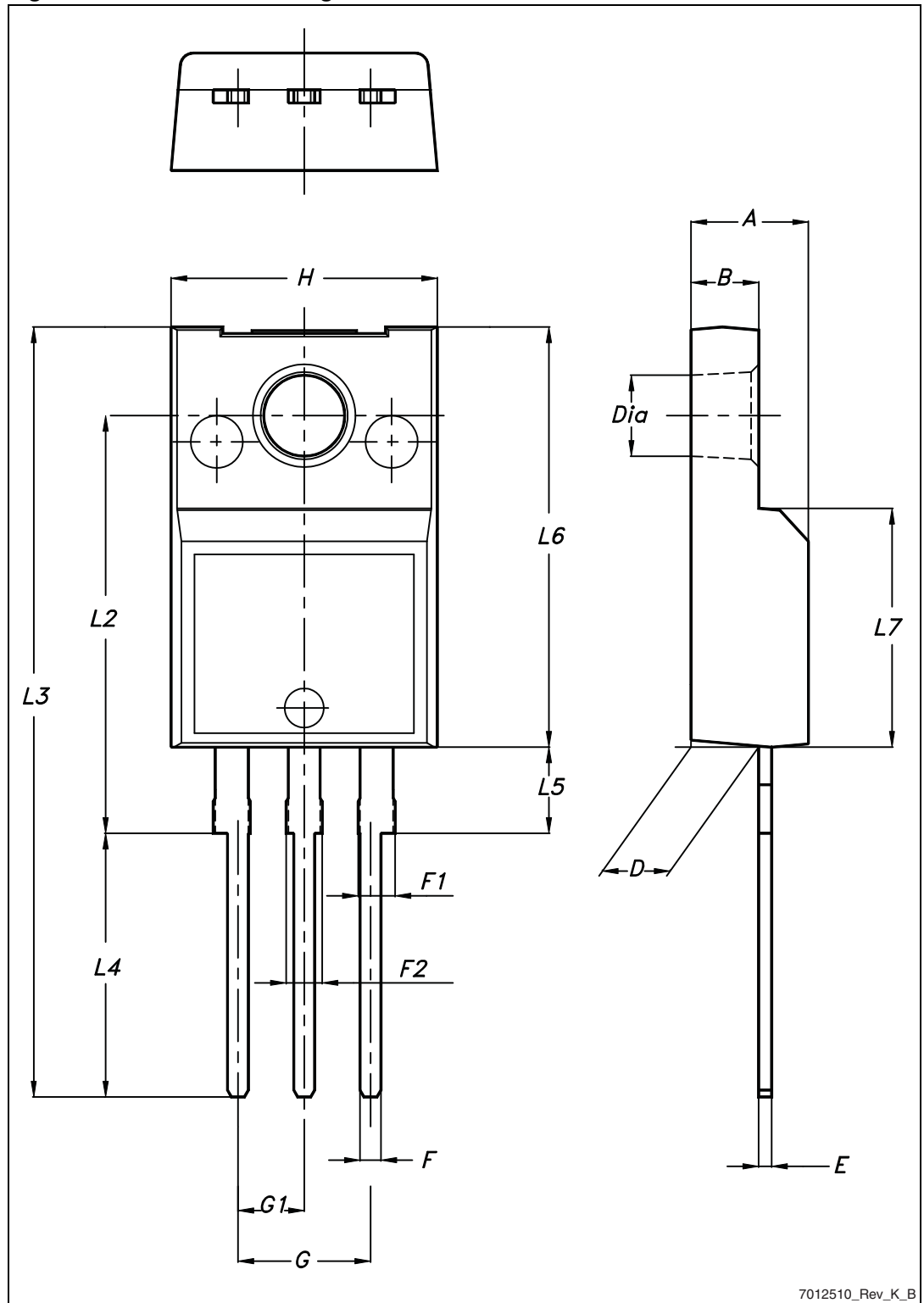


0015988\_typeA\_Rev\_S

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing



7012510\_Rev\_K\_B

## 5 Packaging mechanical data

Table 10. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			



Figure 25. Tape

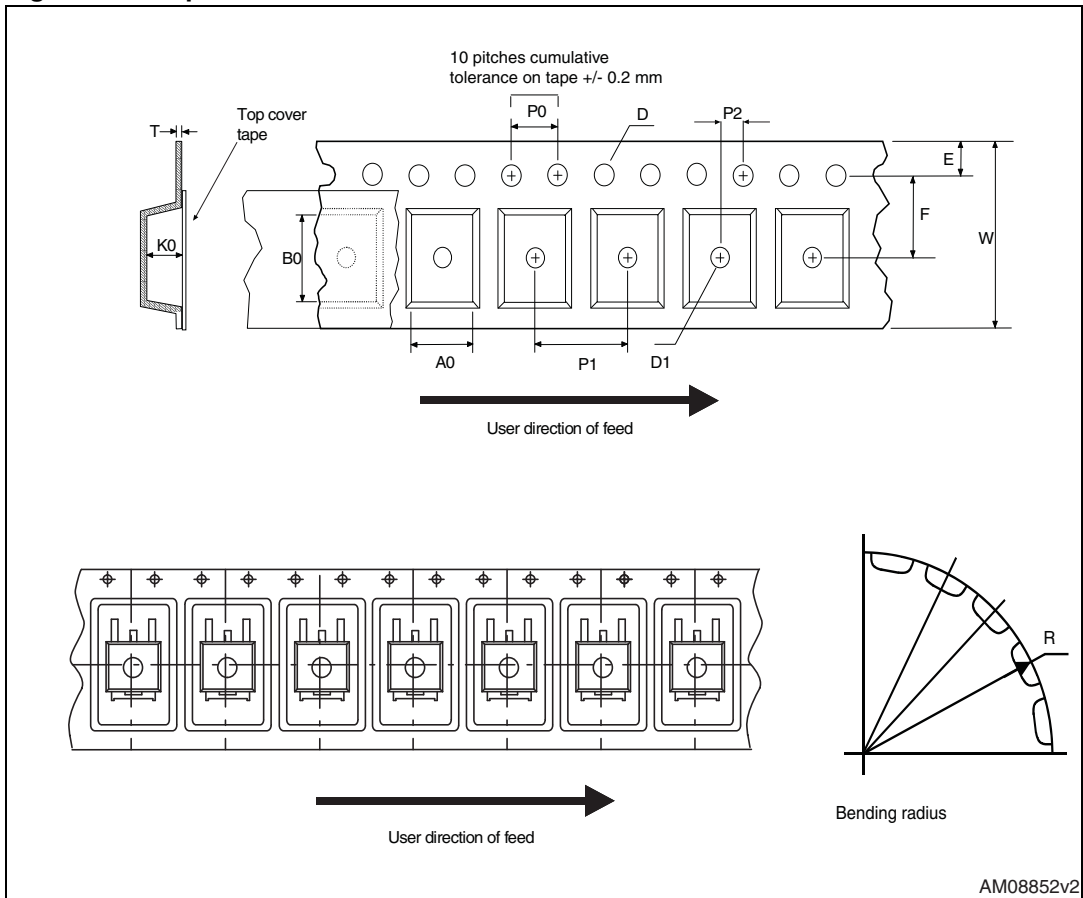
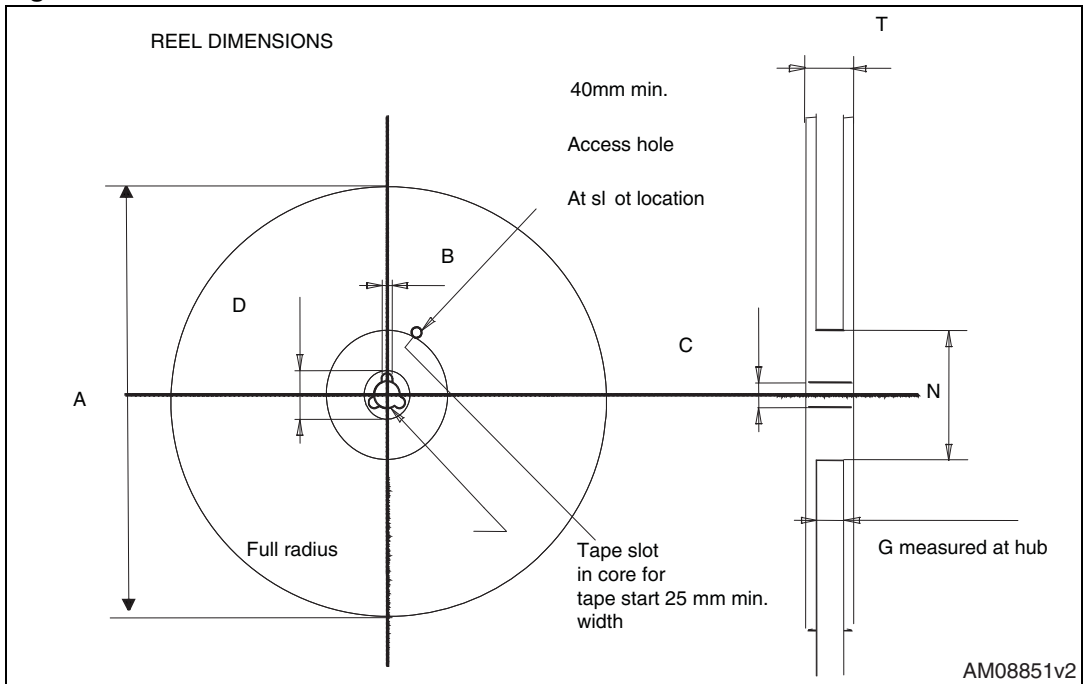


Figure 26. Reel



## 6 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
19-Oct-2005	7	Preliminary document
02-Dec-2005	8	New datasheet according to PCN MLD-PMT/05/1115
28-Mar-2006	9	Inserted ecopack indication
26-Jun-2006	10	New template, no content change
25-May-2012	11	Removed part number STB55NF06-1 in I <sup>2</sup> PAK package <i>Section 4: Package mechanical data</i> and <i>Section 5: Packaging mechanical data</i> have been updated Minor text changes

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)



单击下面可查看定价，库存，交付和生命周期等信息

[>>STMicro\(意法半导体\)](#)